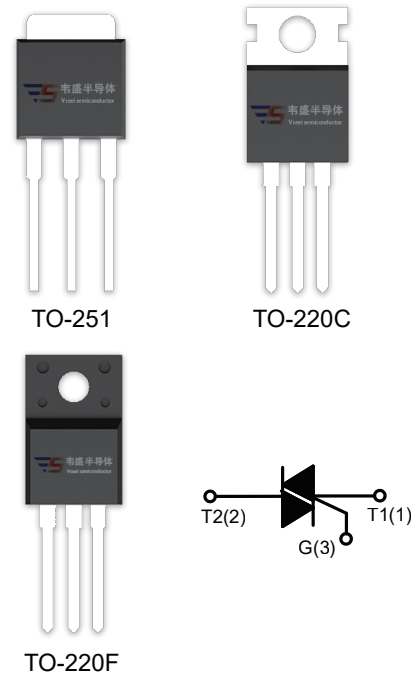


DESCRIPTION:

The BT138-800E SCR series with the parallel resistor between Gate and Cathode are especially recommended for use on straight hair, igniter, anion generator, etc.



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	12	A
V_{DRM}/V_{RRM}	600/800	V

ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T_{stg}	-40-150	°C
Operating junction temperature range		T_j	-40-125	°C
Repetitive peak off-state voltage($T_j=25^{\circ}C$)		V_{DRM}	600/800	V
Repetitive peak reverse voltage($T_j=25^{\circ}C$)		V_{RRM}	600/800	V
Non repetitive surge peak Off-state voltage		V_{DSM}	$V_{DRM} + 100$	V
Non repetitive peak reverse voltage		V_{RSM}	$V_{RRM} + 100$	V
RMS on-state current	TO-251/ TO-220C($T_c=95^{\circ}C$)	$I_{T(RMS)}$	12	A
	TO-220F(Ins) ($T_c=80^{\circ}C$)			
Non repetitive surge peak on-state current (full cycle, $F=50Hz$)		I_{TSM}	95	A
I^2t value for fusing ($t_p=10ms$)		I^2t	45	A^2s

Critical rate of rise of on-state current($I_G=2 \times I_{GT}$)	I - II -III	dI/dt	50	A/ μ s
	IV		10	
Peak gate current		I_{GM}	2	A
Average gate power dissipation		$P_{G(AV)}$	0.5	W
Peak gate power		P_{GM}	5	W

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant		Value			Unit
				D	E	F	
I_{GT}	$V_D=12\text{V } R_L=33\Omega$	I - II -III	MAX	5	10	25	mA
		IV		10	25	70	
V_{GT}		ALL	MAX	1.5			V
V_{GD}	$V_D=V_{DRM} T_j=125^\circ\text{C}$ $R_L=3.3\text{K}\Omega$	ALL	MIN	0.2			V
I_L	$I_G=1.2I_{GT}$	I - III	MAX	15	30	40	mA
		II - IV		20	40	80	
I_H	$I_T=100\text{mA}$		MAX	10	25	30	mA
dV/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^\circ\text{C}$		MIN	20	50	50	V/ μ s

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	$I_{TM}=15\text{A } t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.6	V
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	5	μA
I_{RRM}		$T_j=125^\circ\text{C}$	1	mA

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-220C	1.4	$^\circ\text{C/W}$
		TO-220F(Ins)	2.5	
		TO-251	1.7	

FIG.1: Maximum power dissipation versus RMS on-state current

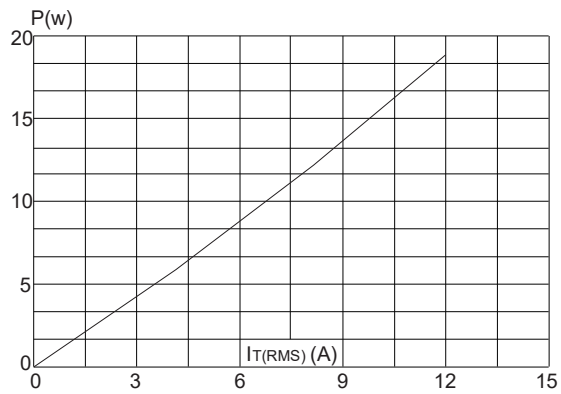


FIG.2: RMS on-state current versus case temperature

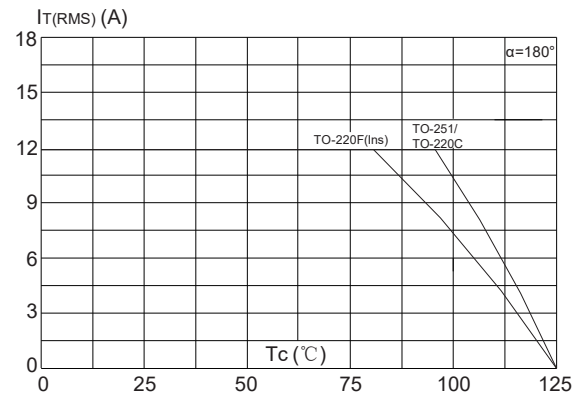


FIG.3: Surge peak on-state current versus number of cycles

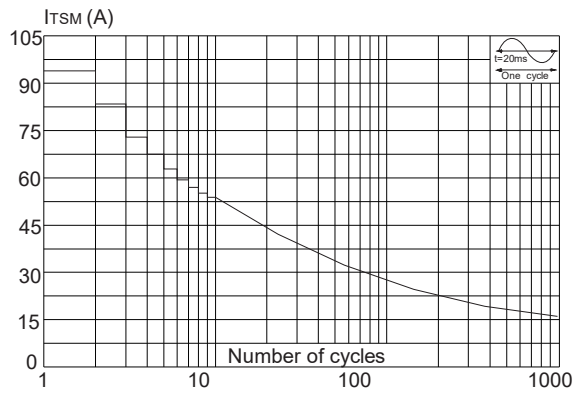


FIG.4: On-state characteristics (maximum values)

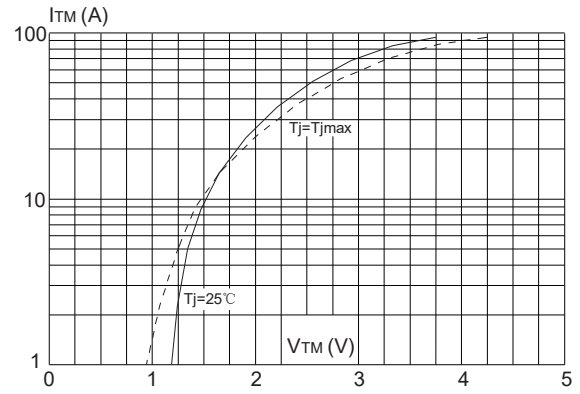


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t (I - II -III: $dI/dt < 50\text{A}/\mu\text{s}$; IV: $dI/dt < 10\text{A}/\mu\text{s}$)
 I_{TSM} (A), I^2t (A^2s)

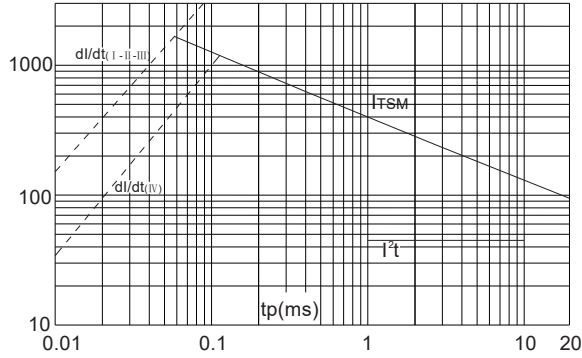


FIG.6: Relative variations of gate trigger current versus junction temperature

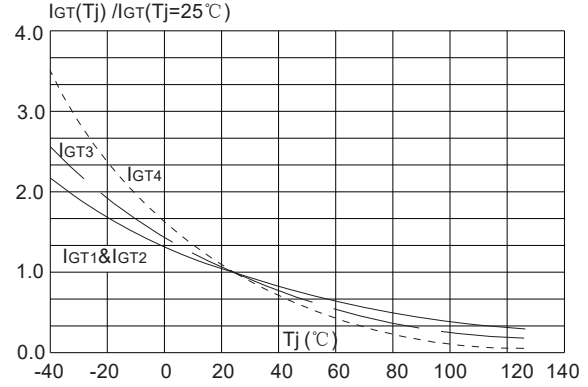


FIG.7: Relative variations of holding current versus junction temperature

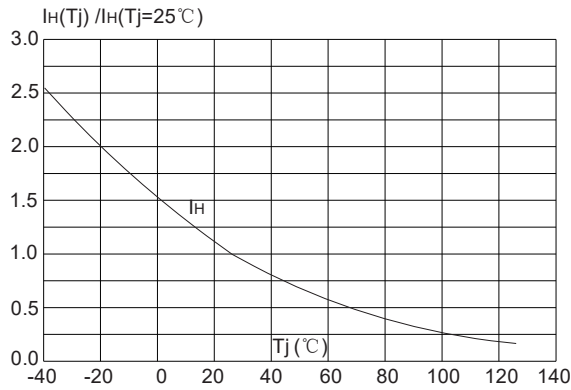


FIG.8: Relative variations of latching current versus junction temperature

